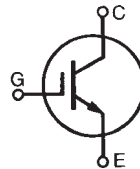


### High Voltage IGBT

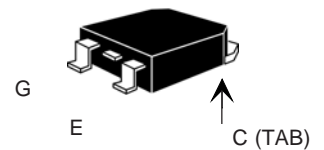
**IXGH 6N170A**  
**IXGT 6N170A**

**V<sub>CES</sub> = 1700 V**  
**I<sub>C25</sub> = 6 A**  
**V<sub>CE(sat)</sub> = 7.0 V**  
**t<sub>fi(typ)</sub> = 32 ns**

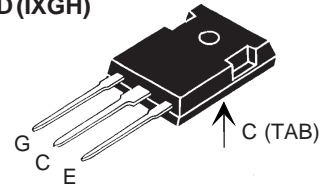


Symbol	Test Conditions	Maximum Ratings	
V <sub>CES</sub>	T <sub>J</sub> = 25°C to 150°C	1700	V
V <sub>CGR</sub>	T <sub>J</sub> = 25°C to 150°C; R <sub>GE</sub> = 1 MΩ	1700	V
V <sub>GES</sub>	Continuous	±20	V
V <sub>GEM</sub>	Transient	±30	V
I <sub>C25</sub>	T <sub>C</sub> = 25°C	6	A
I <sub>C90</sub>	T <sub>C</sub> = 90°C	3	A
I <sub>CM</sub>	T <sub>C</sub> = 25°C, 1 ms	14	A
<b>SSOA (RBSOA)</b>	V <sub>GE</sub> = 15 V, T <sub>VJ</sub> = 125°C, R <sub>G</sub> = 33Ω Clamped inductive load	I <sub>CM</sub> = 12 @ 0.8 V <sub>CES</sub>	A
t <sub>SC</sub>	T <sub>J</sub> = 125°C, V <sub>CE</sub> = 1200 V; V <sub>GE</sub> = 15 V, R <sub>G</sub> = 33Ω	10	μs
P <sub>C</sub>	T <sub>C</sub> = 25°C	75	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
M <sub>d</sub>	Mounting torque (M3)	(TO-247)	1.13/10Nm/lb.in.
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C
<b>Weight</b>		TO-247	6 g
		TO-268	4 g

TO-268 (IXGT)



TO-247 AD (IXGH)



G = Gate,  
E = Emitter,  
C = Collector,  
TAB = Collector

#### Features

- International standard packages  
JEDEC TO-268 and  
JEDEC TO-247 AD
- High current handling capability
- MOS Gate turn-on  
- drive simplicity
- Rugged NPT structure
- Molding epoxies meet UL 94 V-0  
flammability classification

#### Applications

- Capacitor discharge & pulser circuits
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode  
power supplies

#### Advantages

- High power density
- Suitable for surface mounting
- Easy to mount with 1 screw,  
(isolated mounting screw hole)

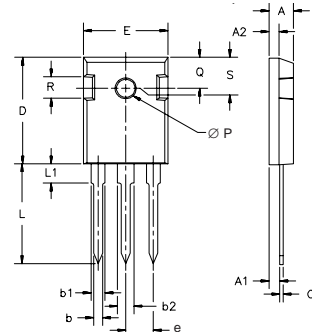
Symbol	Test Conditions	Characteristic Values (T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
BV <sub>CES</sub>	I <sub>C</sub> = 250 μA, V <sub>GE</sub> = 0 V	1700		V
V <sub>GE(th)</sub>	I <sub>C</sub> = 250 μA, V <sub>CE</sub> = V <sub>GE</sub>	3.0		V
I <sub>CES</sub>	V <sub>CE</sub> = 0.8 • V <sub>CES</sub> V <sub>GE</sub> = 0 V		T <sub>J</sub> = 25°C Note 1 T <sub>J</sub> = 125°C	10 μA 500 μA
I <sub>GES</sub>	V <sub>CE</sub> = 0 V, V <sub>GE</sub> = ±20 V			±100 nA
V <sub>CE(sat)</sub>	I <sub>C</sub> = I <sub>C90</sub> , V <sub>GE</sub> = 15 V		T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C	5.5 V 6.5 V

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$g_{fs}$	$I_C = I_{C25}; V_{CE} = 20\text{ V}$ Note 2	2	3.5	S	
$C_{ies}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		330	pF	
$C_{oes}$			23	pF	
$C_{res}$			6	pF	
$Q_G$	$I_C = I_{C90}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		20	nC	
$Q_{GE}$			3.6	nC	
$Q_{GC}$			8	nC	
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_{C25}, V_{GE} = 15\text{ V}$ $R_G = 33\ \Omega, V_{CE} = 0.5 V_{CES}$		46	ns	
$t_{ri}$			40	ns	
$t_{d(off)}$			220	450	ns
$t_{fi}$			32	65	ns
$E_{off}$			0.19	0.40	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = I_{C25}, V_{GE} = 15\text{ V}$ $R_G = 33\ \Omega, V_{CE} = 0.5 V_{CES}$		48	ns	
$t_{ri}$			43	ns	
$E_{on}$			0.7	mJ	
$t_{d(off)}$			230	ns	
$t_{fi}$			41	ns	
$E_{off}$			0.26	mJ	
$R_{thJC}$	(TO-247)			1.65	K/W
$R_{thCK}$			0.25		K/W

Notes: 1. Device must be heatsunk for high temperature leakage current measurements to avoid thermal runaway.

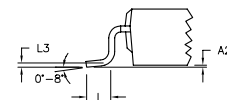
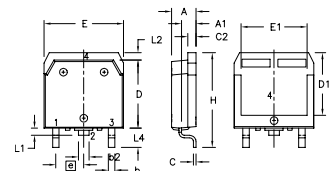
2. Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$

### TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

### TO-268 Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A <sub>1</sub>	2.7	2.9	.106	.114
A <sub>2</sub>	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b <sub>2</sub>	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E <sub>1</sub>	13.3	13.6	.524	.535
e	5.45	BSC	.215	BSC
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3		0.25		.010
L4	3.80	4.10	.150	.161

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	